

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSV)

2SK2698

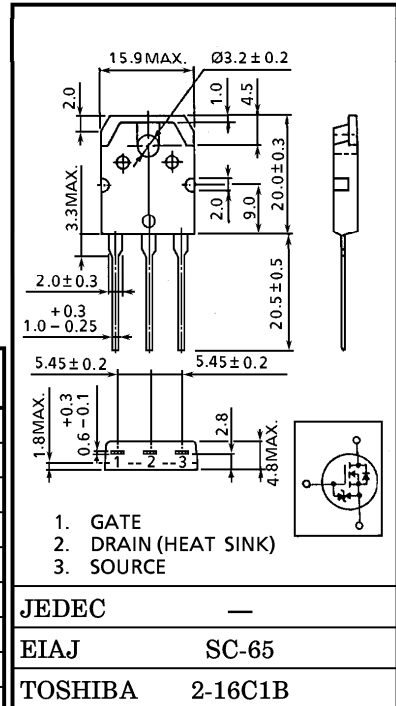
HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS
DC-DC CONVERTER, RELAY DRIVE AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.35 \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 11 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu\text{A}$ (Max.) ($V_{DS} = 500 \text{ V}$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0 \text{ V}$
($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	500	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	500	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	DC	I_D	15 A
	Pulse	I_{DP}	60 A
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	150	W
Single Pulse Avalanche Energy**	E_{AS}	630	mJ
Avalanche Current	I_{AR}	15	A
Repetitive Avalanche Energy*	E_{AR}	15	mJ
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



Weight : 4.6 g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	0.833	$^\circ\text{C/W}$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	$^\circ\text{C/W}$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 4.76 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = 15 \text{ A}$

This transistor is an electrostatic sensitive device.

Please handle with caution.

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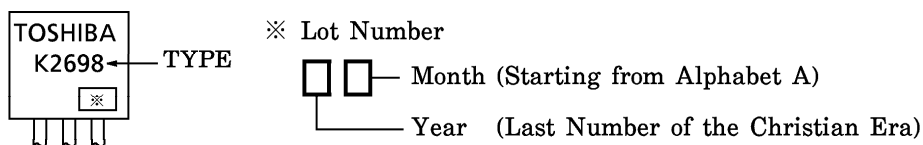
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

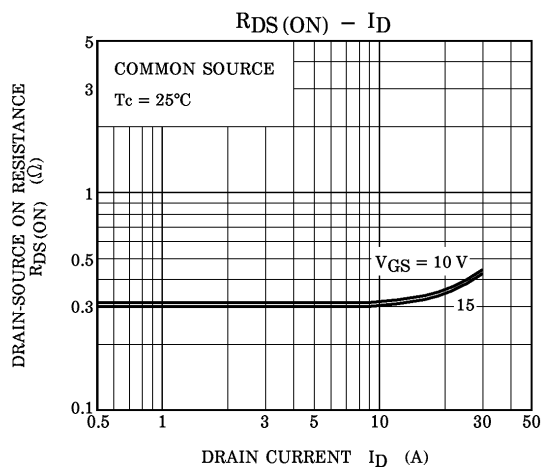
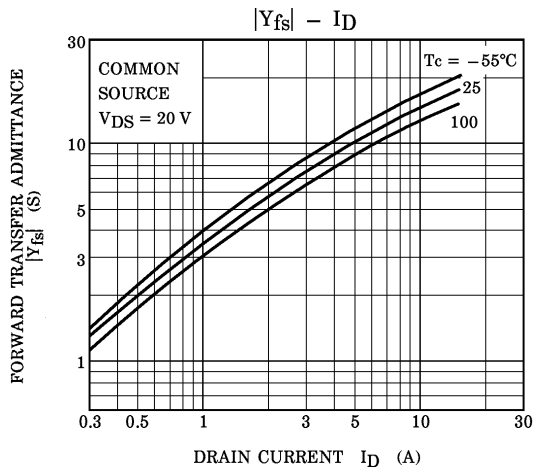
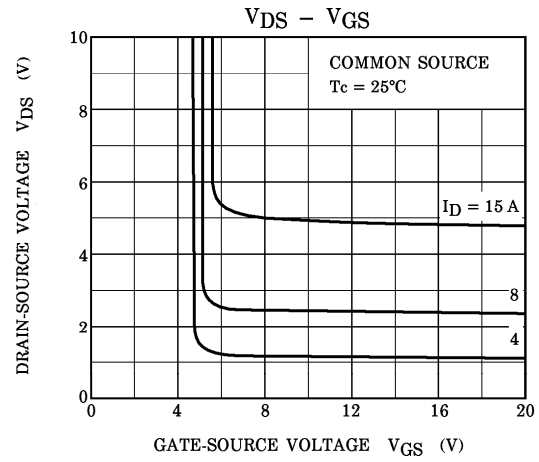
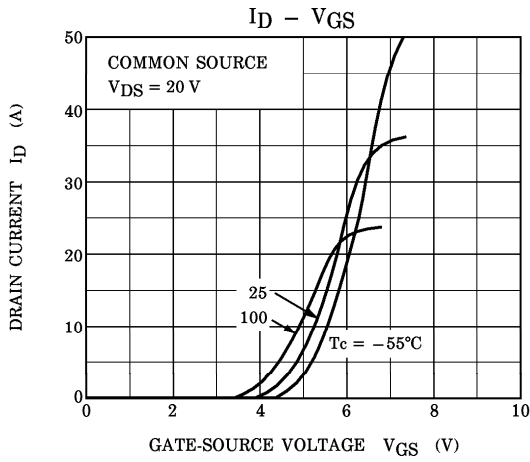
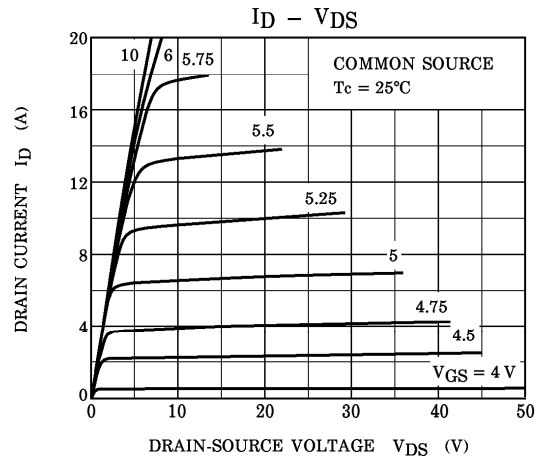
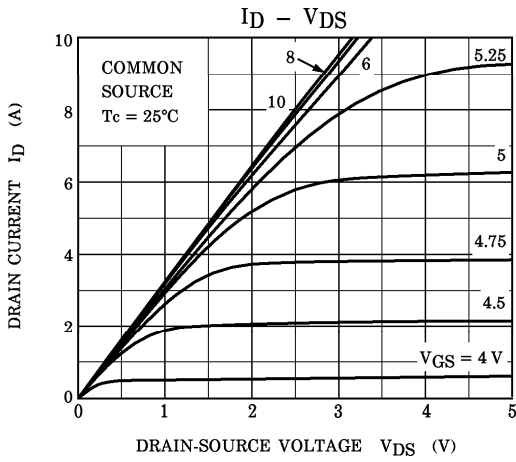
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA	
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 10\ \mu\text{A}, V_{DS} = 0\text{ V}$	± 30	—	—	V	
Drain Cut-off Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	500	—	—	V	
Gate Threshold Voltage	V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	V	
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 7.0\text{ A}$	—	0.35	0.4	Ω	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 7.0\text{ A}$	6	11	—	S	
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2600	—	pF	
Reverse Transfer Capacitance	C_{rss}		—	280	—		
Output Capacitance	C_{oss}		—	880	—		
Switching Time	Rise Time	t_r		—	50	—	ns
	Turn-on Time	t_{on}		—	85	—	
	Fall Time	t_f		—	65	—	
	Turn-off Time	t_{off}		$V_{IN} : t_r, t_f < 5\text{ ns},$ $Duty \leq 1\%, t_w = 10\ \mu\text{s}$	—	260	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	—	58	—	nC	
Gate-Source Charge	Q_{gs}		—	36	—		
Gate-Drain ("Miller") Charge	Q_{gd}		—	22	—		

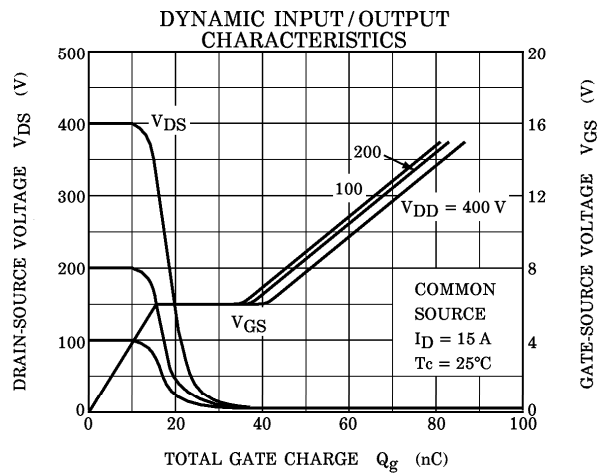
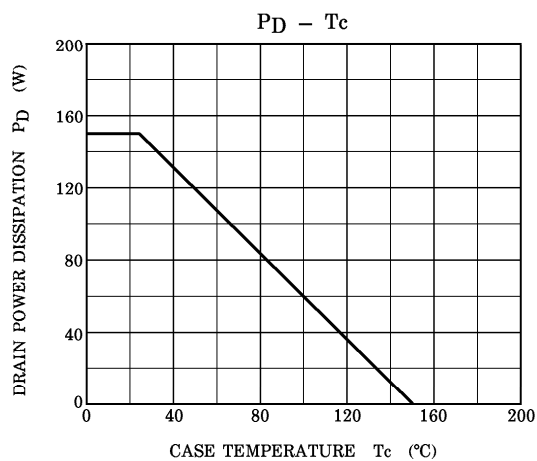
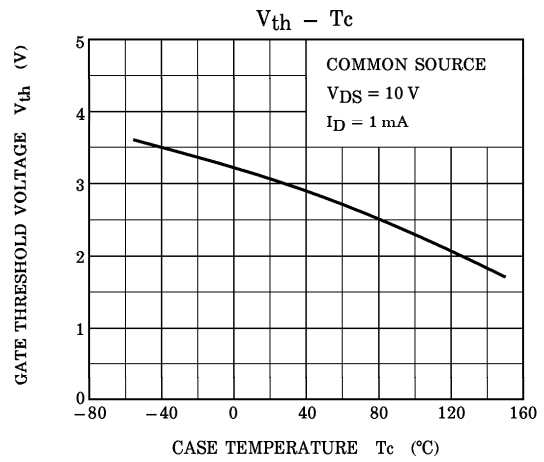
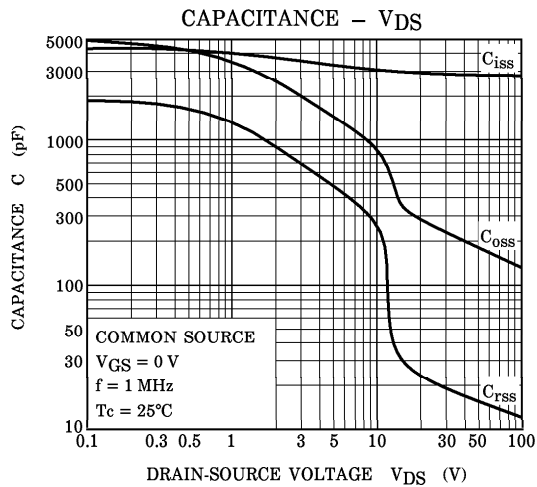
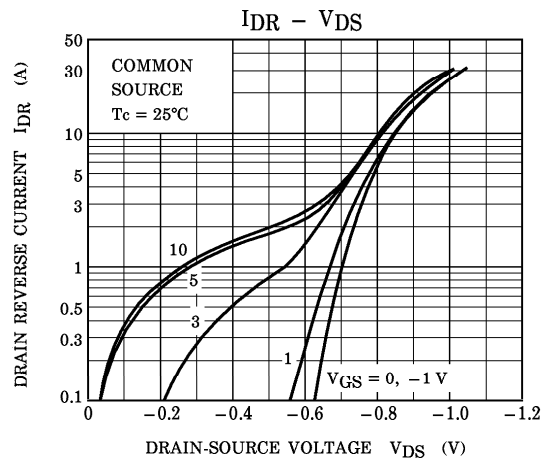
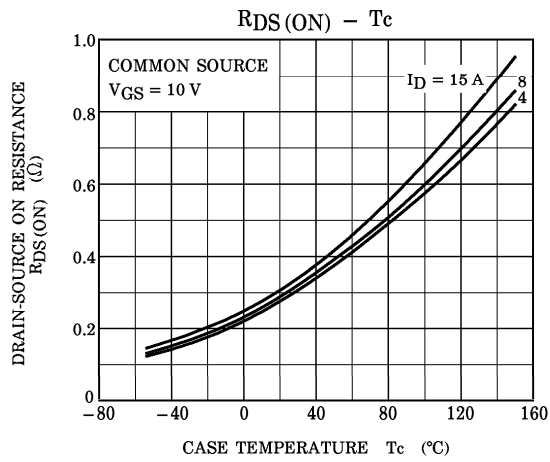
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

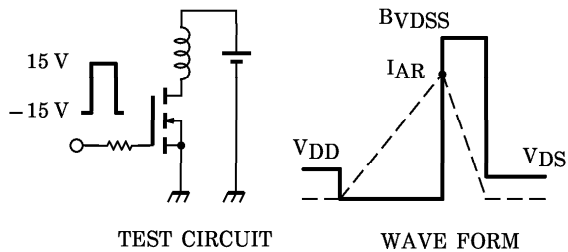
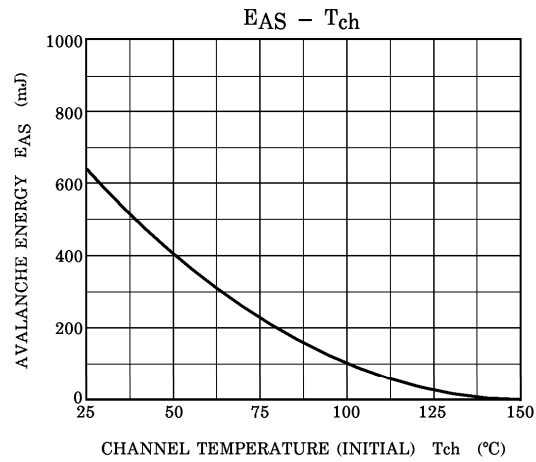
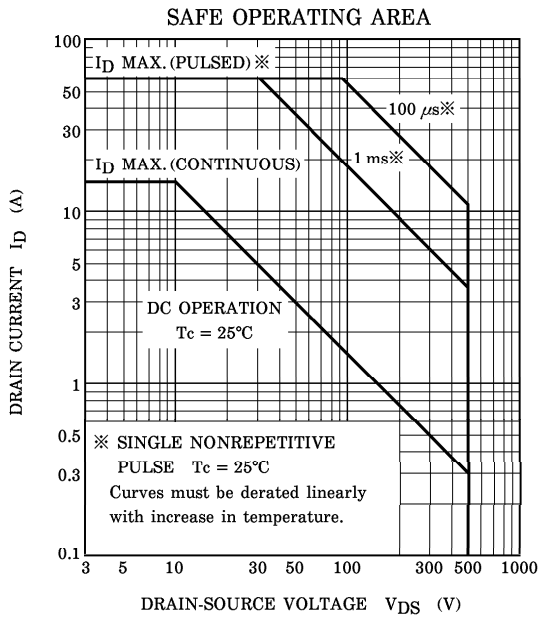
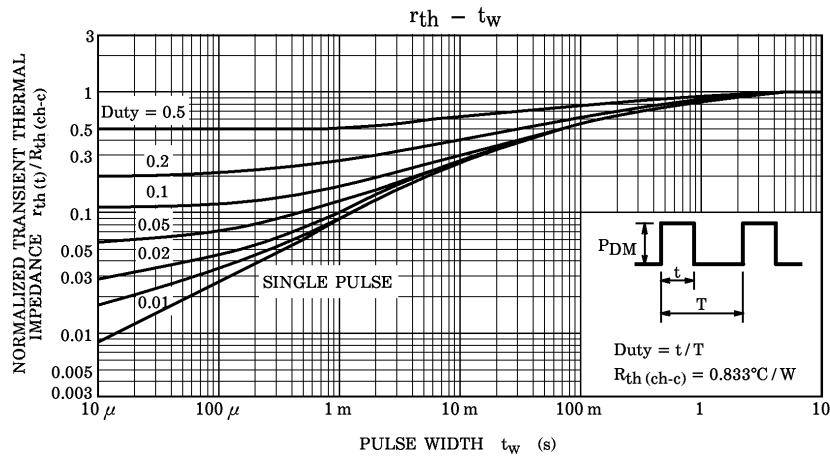
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	15	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	60	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 15\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 15\text{ A}, V_{GS} = 0\text{ V}$	—	400	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	4.3	—	μC

MARKING









Peak $I_{AR} = 15 \text{ A}$, $R_G = 25 \Omega$
 $V_{DD} = 90 \text{ V}$, $L = 4.76 \text{ mH}$ $E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$